UHF power transistor BLW90

Description:
N-P-N silicon planar epitaxial transistor suitable for transmitting applications in class-A, B or C in the UHF and VHF range for a nominal supply voltage of 28 V. The transistor is resistance stabilized and is guaranteed to withstand infinite VSWR at rated output power.

Features:
The transistor is housed in a 1/4" capstan envelope with a ceramic cap.

Data:

MODE OF OPERATION	V_{CE} V	f MHz	P_L W	G_p dB	η %
c.w.	28	470	4	> 11	> 55

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage			
(peak value); V_{BE} = 0	V_{CESM}	max.	60 V
open base	V_{CEO}	max.	30 V
Emitter-base voltage (open collector)	V_{EBO}	max.	4 V
Collector current			
d.c. or average	I_C; $I_{C(AV)}$	max.	0,62 A
(peak value); f > 1 MHz	I_{CM}	max.	2,0 A
Total power dissipation (d.c. and r.f.) up to T_{mb} = 25 °C	P_{tot}	max.	18,6 W
Storage temperature	T_{stg}	–65 to + 150	°C
Operating junction temperature	T_j	max.	200 °C

Drawings:

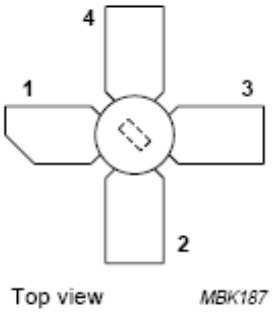

Fig.1 Simplified outline. SOT122A.

PINNING - SOT122A.

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter